# imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

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#### NPN POWER SILICON TRANSISTOR Qualified per MIL-PRF-19500/454

DEVICES
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2N5660 2N5660U3

2N5661 2N5662

2N5663 2N5661U3

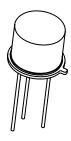
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## ABSOLUTE MAXIMUM RATINGS ( $T_c = +25^{\circ}C$ unless otherwise noted)

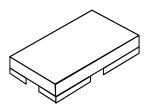
Parameters / Test Conditions	Symbol	2N5660 2N5662	2N5661 2N5663	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	200	300	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	250	400	Vdc
Collector-Emitter Voltage	V <sub>CER</sub>	250	400	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	(	6	Vdc
Base Current	I <sub>B</sub>	0	.5	Adc
Collector Current	I <sub>C</sub>	2.0		Adc
Operating & Storage Junction Temperature Range	T <sub>j</sub> , T <sub>stg</sub>	-65 to +200		°C
		2N5660 2N5661	2N5662 2N5663	
Total Power Dissipation (a) $T_A = +25^{\circ}C^{(1)}$ (b) $T_C = +100^{\circ}C$	P <sub>T</sub>	2.0 <sup>(1)</sup> 20 <sup>(3)</sup>	$1.0_{-15}^{(2)}$	W
Thermal Resistance, Junction-to-Case Junction-to-Ambient	$R_{ ext{ heta}JC} \ R_{ ext{ heta}JA}$	5.0 87.5	6.7 175	°C/W
Thermal Resistance, Junction-to-Case 2N5660U3 2N5661U3	$R_{\theta JC}$	4.5 4.0		°C/W

Π

**TO-66** 2N5660, 2N5661



**TO-5** 2N5662, 2N5663



U3 2N5660U3, 2N5661U3

# Note:

- 1. Derate linearly 11.4mW/°C for  $T_A > +25^{\circ}C$
- 2. Derate linearly  $5.7 \text{mW/}^{\circ}\text{C}$  for  $T_A > +25^{\circ}\text{C}$
- 3. Derate linearly 200mW/°C for  $T_C > +100$ °C
- 4. Derate linearly 150 mW/°C for  $T_C > +100 \text{°C}$

#### ELECTRICAL CHARACTERISTICS ( $T_A = +25^{\circ}C$ , unless otherwise noted)

Parameters / Test Conditions			Min.	Max.	Unit
OFF CHARACTERTICS					
Collector-Emitter Breakdown Vo					
$I_C = 10 \text{mAdc}$	2N5660, U3, 2N5662 2N5661, U3, 2N5663	V <sub>(BR)CEO</sub>	200 300		Vdc
Collector-Base Breakdown Volta $I_C = 10$ mAdc, $R_{BE} = 100\Omega$	ge 2N5660, U3, 2N5662 2N5661, U3, 2N5663	V <sub>(BR)CER</sub>	250 400		Vdc



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# ELECTRICAL CHARACTERISTICS ( $T_A = +25^{\circ}C$ , unless otherwise noted)

Parameters / Test Conditions		Symbol	Min.	Max.	Unit
OFF CHARACTERTICS					
Emitter-Base Breakdown Voltage $I_E = 10 \mu Adc$		V <sub>(BR)EBO</sub>	6.0		Vdc
Collector-Emitter Cutoff Current $V_{CE} = 200$ Vdc $V_{CE} = 300$ Vdc Collector-Base Cutoff Current	2N5660, U3, 2N5662 2N5661, U3, 2N5663	I <sub>CES</sub>		0.2 0.2	μAdc
$V_{CB} = 200 V dc$ $V_{CB} = 250 V dc$ $V_{CB} = 300 V dc$ $V_{CB} = 400 V dc$	2N5660, U3, 2N5662 2N5660, U3, 2N5662 2N5661, U3, 2N5663 2N5661, U3, 2N5663	I <sub>CBO</sub>		0.1 1.0 0.1 1.0	μAdc mAdc μAdc mAdc
ON CHARACTERISTICS (5)	,,	L L			
Forward-Current Transfer Ratio $I_C = 50 \text{mAdc}, V_{CE} = 2.0 \text{Vdc}$ $I_C = 0.5 \text{Adc}, V_{CE} = 5.0 \text{Vdc}$ $I_C = 1.0 \text{Adc}, V_{CE} = 5.0 \text{Vdc}$ $I_C = 2.0 \text{Adc}, V_{CE} = 5.0 \text{Vdc}$	2N5660, U3, 2N5662 2N5661, U3, 2N5663 2N5660, U3, 2N5662 2N5661, U3, 2N5663 All types All types	h <sub>FE</sub>	40 25 40 25 15 5.0	120 75	
Collector-Emitter Saturation Voltage $I_C = 1.0$ Adc, $I_B = 0.1$ Adc $I_C = 2.0$ Adc, $I_B = 0.4$ Adc		V <sub>CE(sat)</sub>		0.4 0.8	Vdc
Base-Emitter Saturation Voltage $I_C = 1.0$ Adc, $I_B = 0.1$ Adc $I_C = 2.0$ Adc, $I_B = 0.4$ Adc		$V_{BE(sat)}$		1.2 1.5	Vdc

# **DYNAMIC CHARACTERISTICS**

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Magnitude of Common Emitter Small–Signal Short-Circuit Forward Current Transfer Ratio $I_C = 0.1$ Adc, $V_{CE} = 5.0$ Vdc, $f = 10$ MHz	h <sub>fe</sub>	2.0	7.0	
Output Capacitance $V_{CB} = 10$ Vdc, $I_E = 0$ , $100$ kHz $\leq f \leq 1.0$ MHz	C <sub>obo</sub>		45	pF

## SWITCHING CHARACTERISTICS

Parameters / Test Conditions		Symbol	Min.	Max.	Unit
Turn-On Time $V_{CC} = 100Vdc; I_C = 0.5Adc; I_{B1} = 15mAdc$ $V_{CC} = 100Vdc; I_C = 0.5Adc; I_{B1} = 25mAdc$	2N5660, U3, 2N5662 2N5661, U3, 2N5663	ton		0.25 0.25	μs
Turn-Off Time $V_{CC} = 100Vdc; I_C = 0.5Adc; I_{B1} = -I_{B2} = 15mAdc$ $V_{CC} = 100Vdc; I_C = 0.5Adc; I_{B1} = -I_{B2} = 25mAdc$	2N5660, U3, 2N5662 2N5661, U3, 2N5663	<sup>t</sup> off		0.85 1.2	μs



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# SAFE OPERATING AREA

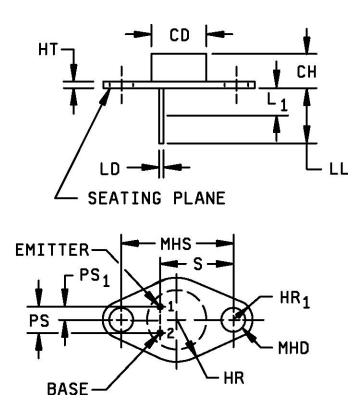
DC Test	
$T_{\rm C} = +100^{\circ}{\rm C}, 1 \text{ cycle}, t \ge 1.0{\rm s}$	
Test 1	
$V_{CE} = 10Vdc, I_{C} = 2.0Adc$	2N5660, U3, 2N5661, U3
$V_{CE} = 7.5 V dc, I_C = 2.0 A dc$	2N5662, 2N5663
Test 2	
$V_{CE} = 40 V dc, I_{C} = 500 m A dc$	2N5660, U3, 2N5661, U3
$V_{CE} = 25 V dc$ , $I_C = 600 m A dc$	2N5662, 2N5663
Test 3	
$V_{CE} = 200 V dc, I_C = 36 m A dc$	2N5660, U3
$V_{CE} = 200 V dc, I_C = 27 m A dc$	2N5662
Test 4	
$V_{CE} = 300 V dc, I_C = 19 m A dc$	2N5661, U3
$V_{CE} = 300 V dc$ , $I_C = 14 m A dc$	2N5663

(5) Pulse Test: Pulse Width =  $300\mu$ s, Duty Cycle  $\leq 2.0\%$ .



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# **PACKAGE DIMENSIONS**



	Dimensions				
Ltr	Inc	hes	Millir	neters	Notes
	Min	Max	Min	Max	
CD	.470	.500	11.94	12.70	7
СН	.250	.340	6.35	8.64	
HR		.350		8.89	
$HR_1$	.115	.145	2.92	3.68	4
HT	.050	.075	1.27	1.91	
LD	.028	.034	0.71	0.86	4, 6
LL	.360	.500	9.14	12.70	4
$L_1$		.050		1.27	4,6
MHD	.142	.152	3.61	3.86	4
MHS	.958	.962	24.33	24.43	
PS	.190	.210	4.83	5.33	3
$PS_1$	.093	.107	2.36	2.72	3
S	.570	.590	14.48	14.99	3

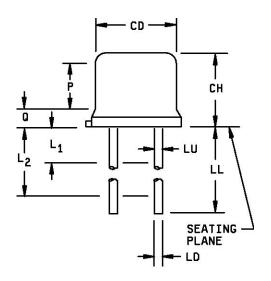
# NOTES:

- 1 Dimensions are in inches.
- 2 Millimeters are given for general information only.
- These dimensions should be measured at points .050 inch (1.27 mm) +.005 inch (0.13 mm) -.000 inch (0.00 mm) below seating plane. When gauge is not used, measurement will be made at the seating plane.
- 4 Two places.
- 5 The seating plane of the header shall be flat within .001 inch (0.03 mm) concave to .004 inch (0.10 mm) convex inside a .930 inch (23.62 mm) diameter circle on the center of the header and flat within .001 inch (0.03 mm) concave to .006 inch (0.15 mm) convex overall.
- 6 Lead diameter shall not exceed twice LD within  $L_1$ .
- 7 Body contour is optional within zone defined by CD.
- 8 In accordance with ASME Y14.5M, diameters are equivalent to \$\phi\$x symbology.
- 9 Lead 1 is emitter, lead 2 is base, and case is collector.

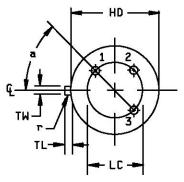
FIGURE 1. Physical dimensions, 2N5660 and 2N5661, (similar to TO-66).



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	Dimensions					
Ltr	Inc	hes	Millimeters		Notes	
	Min	Max	Min	Max		
CD	.305	.355	7.75	9.02		
СН	.240	.260	6.10	6.60		
HD	.335	.370	8.51	9.40		
LC	.200	) TP	5.08	3 TP	6	
LD	.016	.021	0.41	0.53	7	
LL	1.500	1.750	38.10	44.45	7	
LU	.016	.019	0.407	0.482	7	
$L_1$		.050		1.27	7	
$L_2$	.250		6.35		7	
TL	.029	.045	0.74	1.14	3	
TW	.028	.034	0.712	0.863	9	
Р	.100		2.54			
Q		.050		1.27	4	
r		.010		0.25	10	
α	45°	ТР	45°	TP	6	



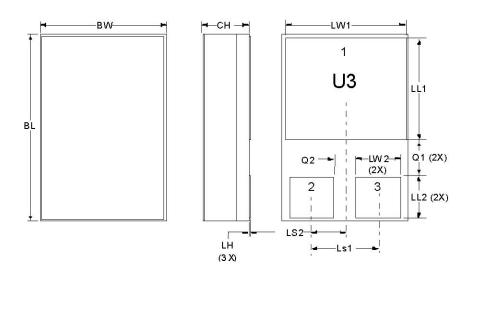
#### NOTES:

- 1. Dimensions are in inches.
- 2. Millimeters are given for general information only.
- 3. Symbol TL is measured from HD maximum.
- 4. Details of outline in this zone are optional.
- 5. Symbol CD shall not vary more than .010 inch (0.25 mm) in zone P. This zone is controlled for automatic handling.
- 6. Leads at gauge plane .054 inch (1.37 mm) +.001 inch (0.03 mm) .000 inch (0.00 mm) below seating plane shall be within .007 inch (0.18 mm) radius of TP relative to tab. Device may be measured by direct methods or by gauge.
- 7. Symbol LU applies between L1 and L2. Dimension LD applies between L2 and LL minimum.
- 8. Lead number three is electrically connected to case.
- 9. Beyond r maximum, TW shall be held for a minimum length of .011 inch (0.28 mm).
- 10. Symbol r applied to both inside corners of tab.
- 11. In accordance with ASME Y14.5M, diameters are equivalent to  $\varphi x$  symbology.
- 12. Lead 1 is emitter, lead 2 is base, and lead 3 is collector.

FIGURE 2. Physical dimensions, 2N5662 and 2N5663, (similar to TO-5)



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	Dimensions					
Symbol	Inc	hes	Millir	neters		
	Min Max		Min	Max		
BL	.395	.405	10.04	10.28		
BW	.291	.301	7.40	7.64		
СН	.1085	.1205	2.76	3.06		
LH	.010	.020	0.25	0.51		
$LW_1$	.281	.291	7.14	7.39		
$LW_2$	.090	.100	2.29	2.54		
LL <sub>1</sub>	.220	.230	5.59	5.84		
$LL_2$	.115	.125	2.93	3.17		
$LS_1$	.150	BSC	3.81	BSC		
$LS_2$	.075	BSC	1.91 BSC			
$Q_1$	.030		0.762			
Q <sub>2</sub>	.030		0.762			
Term 1	Collector					
Term 2	Base					
Term 3	Emitter					

FIGURE 3. Physical dimensions, 2N5660U3 and 2N5661U3(U3).